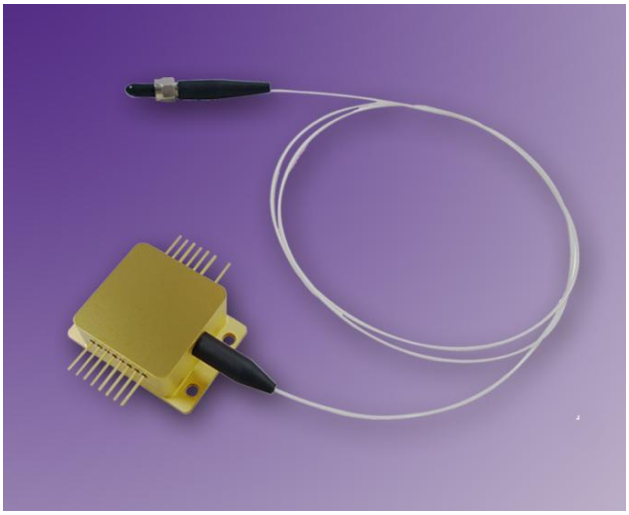
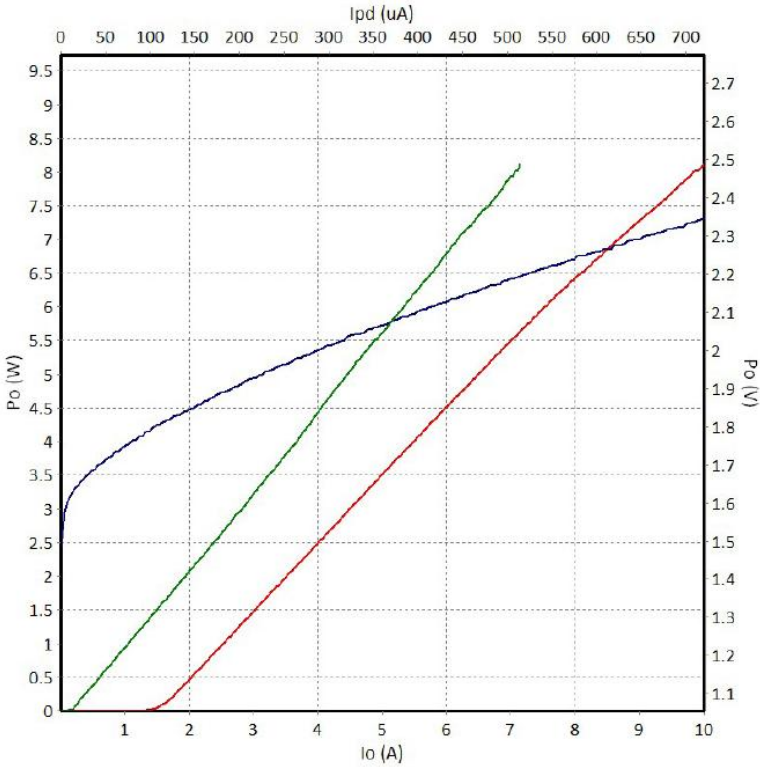
808nm 8W Laser Diode Module

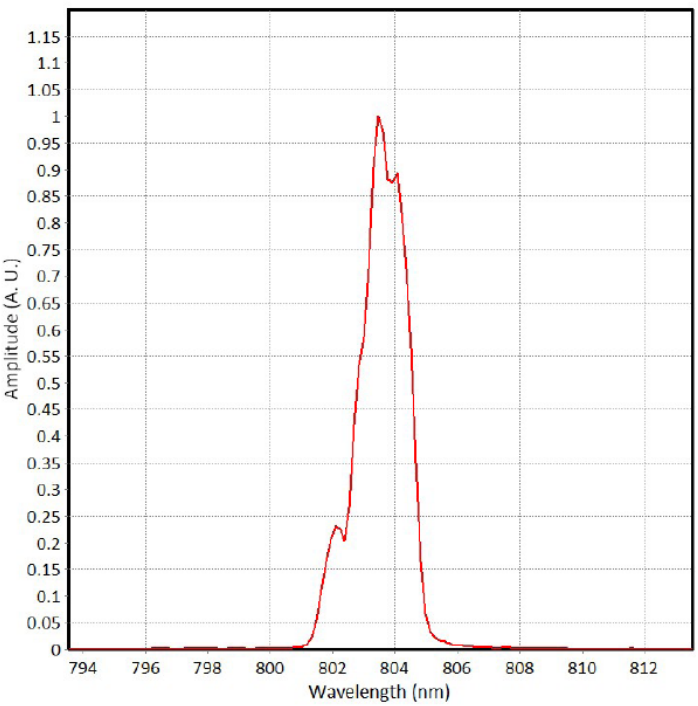
R808±10–8WF–15HHL–PT



Feature
Output power: 8W
Wavelength: 808±10nm
Fiber core: 200 μm, 0.22NA
Aiming beam: 650nm
Application
Medical use
Material processing

808nm 8W Characteristics (25˚C)





Typical Device Performance(25℃)

Parameter		Symbol	Typical Value	Unit
			R808±10–8WF–15HHL–PT	
Optical	CW Output Power	P_{op}	8	W
	Center Wavelength	λ_c	808±10	nm
	Spectral Width	$\Delta\lambda$	＜6	nm
	Temperature drift of wavelength	$\Delta\lambda/\Delta T$	0.3	nm/℃
Aiming Beam	Output Power	P_a	2	mW
	Wavelength	λ_a	650±10	nm
	Voltage	V_a	2.2,5.0	V
Electrical	Threshold Current	I_{th}	1.6	A
	Operating Current	I_{op}	10	A
	Operating Voltage	V_{op}	2.4	V
	Slope Efficiency	η_{es}	0.95	W/A
	PD Current	I_{PD}	＜2000	μA
	Thermistor	R_t	10±5%/3450	kΩ/β(25℃)
	TEC Max Current	I_{tmax}	6.0	A
	TEC Max Voltage	V_{tmax}	9.8	V
Fiber	Fiber Core Diameter	d_{core}	200	μm
	Connector	-	FC/PC,ST,SMA905	-

Other Parameters

Parameter	Operating Temperature /℃	Operating Relative Humidity /%	Storage Temperature /℃	Storage Relative Humidity /%	Lead Soldering Temperature(max/℃)
Min	10	-	-20	-	-
Max	30	75	80	70	250(10Sec.)

Package Dimensions (mm)

Pin	Function	Pin	Function
1	Case	9	-
2	Laser(+)	10	-
3	Thermistor	11	-
4	Thermistor	12	-
5	Laser(-)	13	Aiming Beam LD(+)
6	PD(P)	14	Aiming Beam LD(-)
7	PD(N)	15	TEC(+)
8	TEC(-)